

Description

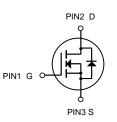
The BSS138BKW,115 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 60V I_D = 0.115A$ $R_{DS(ON)} < 3\Omega @ V_{GS} = 10V$







N-Channel MOSFET

Application

Battery protection Load switch Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
BSS138BKW,115	SOT-323	72K	3000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Symbol Parameter		Unit	
Vds	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	0.115	A	
P _D	Maximum Power Dissipation	0.2	W	
Тյ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	625	°C /W	



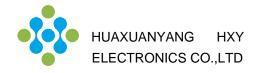
Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0 V, I _D =250 µA	60			V
Gate-Threshold Voltage	V _{(GS)th}	V _{DS} =V _{GS} , I _D =250 μA	1	1.6	2.5	v
Gate-body Leakage	I _{GSS}	V _{DS} =0 V, V _{GS} =±20 V			±80	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60 V, V _{GS} =0 V			80	nA
On-state Drain Current	I _{D(on)}	V _{GS} =10 V, V _{DS} =7 V	500			mA
		V _{GS} =10 V, I _D =115mA		1.3	3	Ω
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =50mA		2	5	
Forward Trans conductance	g _{fs}	V _{DS} =10 V, I _D =200mA	80			ms
	V _{DS(on)}	V _{GS} =10V, I _D =500mA			3.75	V
Drain-source on-voltage		V _{GS} =5V, I _D =50mA			0.375	V
Diode Forward Voltage	V _{SD}	I _S =115mA, V _{GS} =0 V	0.55		1.2	V
Input Capacitance *	C _{iss}				50	
Output Capacitance *	Coss	V _{DS} =25V, V _{GS} =0V, f=1MHz			25	pF
Reverse Transfer Capacitance *	C _{rss}	1			5	

VITCHING TIME

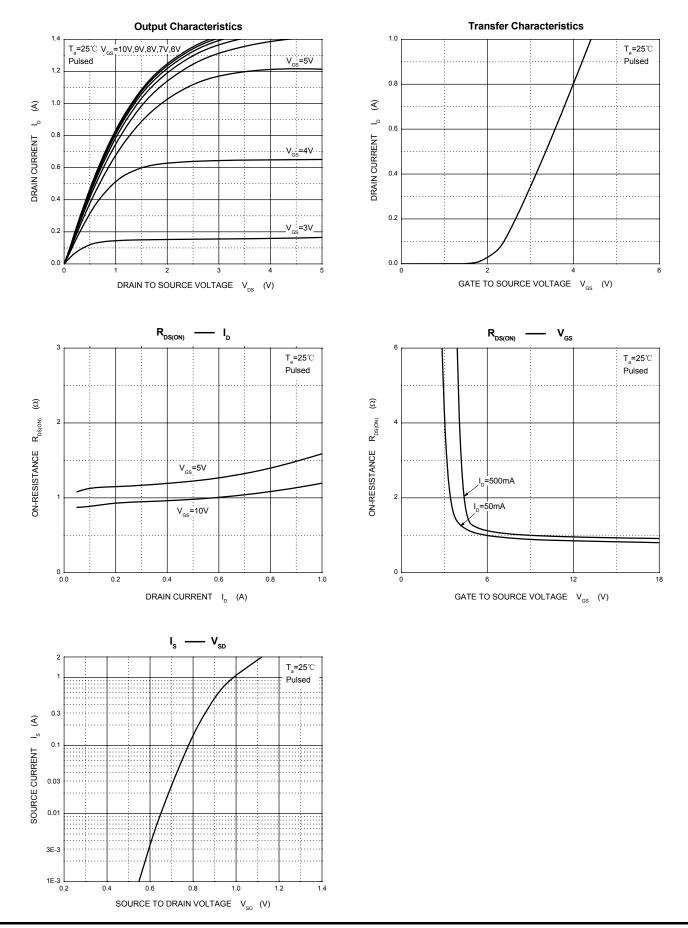
Turn-on Time *	t _{d(on)}	$V_{DD}=25 V, R_{L}=50\Omega,$		20		
Turn-off Time∗	t _{d(off)}	I _D =500mA,V _{GEN} =10 V R _G =25Ω		40	ns	

*These parameters have no way to verify.



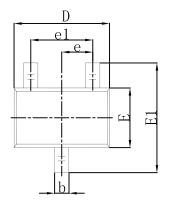
BSS138BKW,115 N-Channel Enhancement Mode MOSFET

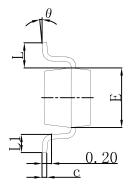
Typical Characteristics

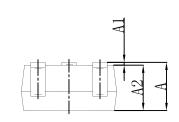




SOT-323 Package Outline Dimensions







Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650) TYP	0.026	6 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
K	0°	8°	0°	8°	



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